

Claim 60 (withdrawn): The method of claim 59 wherein the conductive material comprises one or more of platinum, iridium, ruthenium, and tantalum.

Claim 61 (previously presented): The method of claim 54 wherein the surface comprises a barrier material.

Claim 62 (withdrawn): The method of claim 61 wherein the barrier material comprises one or both of tantalum silicon nitride and tantalum nitride.

Claim 63 (previously presented): The method of claim 54 wherein the pad comprises polyurethane.

Claim 64 (previously presented): The method of claim 54 wherein at least some of the particles comprise silica.

Claim 65 (previously presented): The method of claim 54 wherein the surface comprises at least two layers, a first conductive layer of the two layers comprising N and Si, and a second conductive layer of the two layers comprising N.

Claim 66-73 (cancelled).

Claim 74 (previously presented): A material removal method comprising
providing a substrate supporting a conductive-material-comprising layer, the
conductive-material-comprising layer having an organic-material-comprising layer
thereover;
selectively removing at least a portion of the organic-material-comprising layer
with a first polishing process utilizing a first liquid to thereby expose at least a portion of
an upper surface of the conductive-material-comprising layer, wherein the first liquid is
substantially unreactive with the conductive-material-comprising layer and comprises
less than or equal to 0.1 weight percent particles at an initiation of the removing; and
removing at least a portion of the conductive-material-comprising layer with a
second polishing process utilizing a second liquid.

Claim 75 (previously presented): The method of claim 74 wherein the conductive-
material-comprising layer comprises one or more of platinum, iridium, ruthenium, and
tantalum.

Claim 76 (previously presented): The method of claim 74 wherein the organic-material-
comprising layer comprises one or more of photoresist, non-photosensitive resist and
polyimide.

Claim 77 (previously presented): The method of claim 74 wherein the first polishing
process comprises removing at least a portion of the organic-material-comprising layer
with a chemical mechanical polishing pad and the first liquid.

Claim 78 (previously presented): The method of claim 77 wherein the second polishing process comprises removing at least a portion of the conductive-material-comprising layer with the chemical mechanical polishing pad and the second liquid.

Claim 79 (previously presented): The method of claim 74 wherein the first liquid comprises water.

Claim 80 (previously presented): The method of claim 74 wherein the first liquid comprises one or both of ammonia and TMAH.

Claim 81 (previously presented): The method of claim 74 wherein the second liquid comprises less than or equal to approximately 0.1 weight percent particles at an initiation of the removing of the conductive-material-comprising layer.

Claim 82 (previously presented): The method of claim 74 wherein the second liquid comprises particles.

Claim 83 (previously presented): The method of claim 74 wherein a composition of the second liquid is different than a composition of the first liquid.

Claim 84 (previously presented): The method of claim 74 wherein the second liquid is reactive with the conductive-material-comprising layer.

Claim 85 (previously presented): The method of claim 74 wherein the conductive-material-comprising layer comprises a barrier material.

Claim 86 (withdrawn): The method of claim 77 wherein the barrier material comprises one or both of tantalum silicon nitride and tantalum nitride.